Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 2/4/02

JAMES T. HAGLER REG. NO 40,631

Req. No. 32, 30

SCH/smr

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VERSION TO SHOW CHANGES MADE

In the Claims:

Claims 2, 20, 23, and 36 have been amended as follows.

2. (Amended) A method for manufacturing a semiconductor device comprising steps of:

forming a semiconductor film over a substrate; and irradiating said semiconductor film by scanning with at least two pairs of linear infrared lights in a predetermined direction,

wherein [one] at least two of said linear infrared lights
[is] are located over said substrate and the other [one] at
least two of said linear infrared lights [is] are located at a
backside of said substrate.

20. (Amended) A method for manufacturing semiconductor device comprising the steps of:

i rming an amorphous semi-onductor film over a substrate;

repstalling the semiconfluctor illm by comming with an least two pairs of upper and lower linear infrared lights in a treferenmine; lineation,

linear infrared light [is] <u>are</u> located at a backside of said substrate, and

wherein said predetermined direction is seincident with a direction of crystal growth in the semiconductor film.

29. (Amended) A method for manufacturing semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate; and

crystallizing the semiconductor film by scanning the semiconductor film with at least two pairs of upper and lower linear infrared lights in a direction in order to form and move a temperature gradient the semiconductor film,

wherein said at least two upper linear infrared light [is] are located over said semiconductor film and said at least two lower linear infrared light [is] are located at an underside of said semiconductor film, and

wherein said direction is a incident with a direction of the class with a deep received in the semiconomy or ridge.

36. (Amended) A method for manufacturing a semiconductor inv. we imprise the steps of the semiconductor inv. we imprise the semiconductor inv. we imprise the semiconductor in the semiconductor inv. we imprise the semiconductor in the semico

crystallizing said semiconductor film by irradiating said semiconductor film with at least two pairs of linear infrared lights while moving said substrate in a perpendicular to the linear infrared lights,

wherein [one] at least two of said linear infrared lights [is] are located over said substrate and the other [one] at least two of said linear infrared lights [is] are located at a backside of said substrate, and

wherein an irradiating direction is coincident with a direction of crystal growth to be proceeded in the semiconductor film.